



FCP20N60 / FCPF20N60

N-Channel SuperFET® MOSFET

600 V, 20 A, 190 mΩ

Features

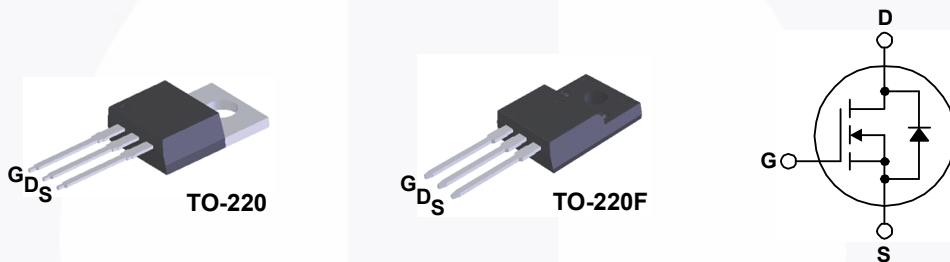
- 650V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 150 \text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 75 \text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(\text{eff.})} = 165 \text{ pF}$)
- 100% Avalanche Tested

Applications

- Solar Inverter
- AC-DC Power Supply

Description

SuperFET® MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.



Absolute Maximum Ratings

Symbol	Parameter	FCP20N60	FCPF20N60	Unit
V_{DSS}	Drain-Source Voltage	600		V
I_D	Drain Current	20	20*	A
	- Continuous ($T_C = 25^\circ\text{C}$)	12.5	12.5*	A
I_{DM}	Drain Current	60	60*	A
V_{GSS}	Gate-Source Voltage	± 30		V
E_{AS}	Single Pulsed Avalanche Energy	690		mJ
I_{AR}	Avalanche Current	20		A
E_{AR}	Repetitive Avalanche Energy	20.8		mJ
dv/dt	Peak Diode Recovery dv/dt	4.5		V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	208	39	W
	- Derate Above 25°C	1.67	0.3	$W/\text{ }^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300		$^\circ\text{C}$

*Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FCP20N60	FCPF20N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.6	3.2	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^\circ\text{C/W}$

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCP20N60	FCP20N60	TO-220	Tube	N/A	N/A	50 units
FCPF20N60	FCPF20N60	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}, T_J = 25^\circ\text{C}$	600	-	-	V
		$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}, T_J = 150^\circ\text{C}$	-	650	-	V
$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C	-	0.6	-	$\text{V}/^\circ\text{C}$
BV_{DS}	Drain-Source Avalanche Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 20 \text{ A}$	-	700	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μA
		$V_{DS} = 480 \text{ V}, T_C = 125^\circ\text{C}$	-	-	10	μA
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	± 100	nA

On Characteristics

$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	3.0	-	5.0	V
$R_{DS(\text{on})}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	0.15	0.19	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40 \text{ V}, I_D = 10 \text{ A}$	-	17	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	2370	3080	pF
C_{oss}	Output Capacitance		-	1280	1665	pF
C_{rss}	Reverse Transfer Capacitance		-	95	-	pF
C_{oss}	Output Capacitance	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	65	85	pF
$C_{oss(\text{eff.})}$	Effective Output Capacitance	$V_{DS} = 0 \text{ V to } 400 \text{ V}, V_{GS} = 0 \text{ V}$	-	165	-	pF
Q_g	Total Gate Charge at 10V	$V_{DS} = 480 \text{ V}, I_D = 20 \text{ A}, V_{GS} = 10 \text{ V}$	-	75	98	nC
Q_{gs}	Gate to Source Gate Charge	(Note 4)	-	13.5	18	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	36	-	nC

Switching Characteristics

$t_{d(\text{on})}$	Turn-On Delay Time	$V_{DD} = 300 \text{ V}, I_D = 20 \text{ A}, V_{GS} = 10 \text{ V}, R_G = 25 \Omega$	-	62	135	ns
t_r	Turn-On Rise Time		-	140	290	ns
$t_{d(\text{off})}$	Turn-Off Delay Time		-	230	470	ns
t_f	Turn-Off Fall Time		(Note 4)	-	65	140

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	20	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	60	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{SD} = 20 \text{ A}$	-	-	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{SD} = 20 \text{ A}, dI_F/dt = 100 \text{ A}/\mu\text{s}$	-	530	-	ns
Q_{rr}	Reverse Recovery Charge		-	10.5	-	μC

Notes:

- 1: Repetitive rating: pulse-width limited by maximum junction temperature.
- 2: $I_{AS} = 10 \text{ A}, V_{DD} = 50 \text{ V}, R_G = 25 \Omega$, starting $T_J = 25^\circ\text{C}$.
- 3: $I_{SD} \leq 20 \text{ A}, dI/dt \leq 200 \text{ A}/\mu\text{s}, V_{DD} \leq \text{BV}_{\text{DSS}}$, starting $T_J = 25^\circ\text{C}$.
- 4: Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

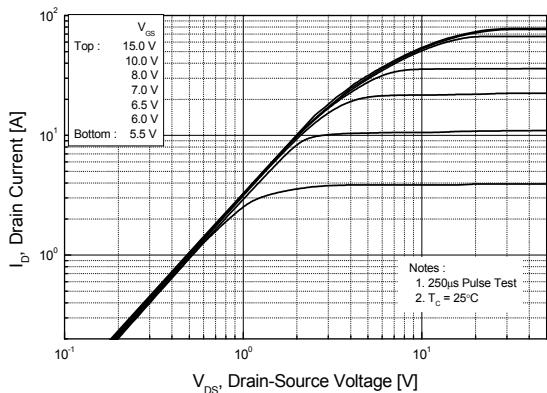


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

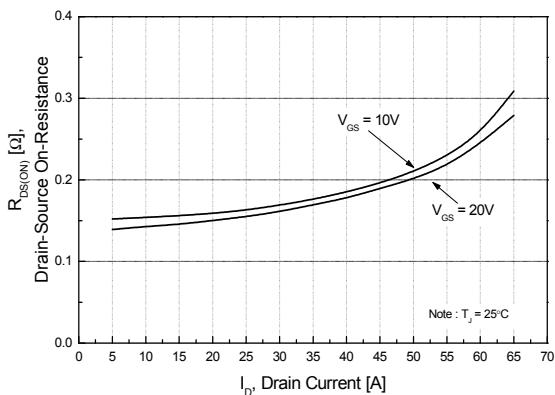


Figure 2. Transfer Characteristics

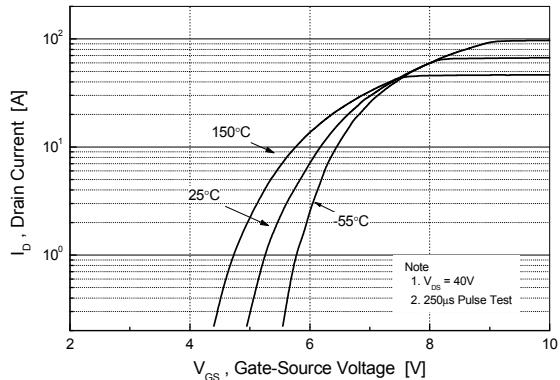


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

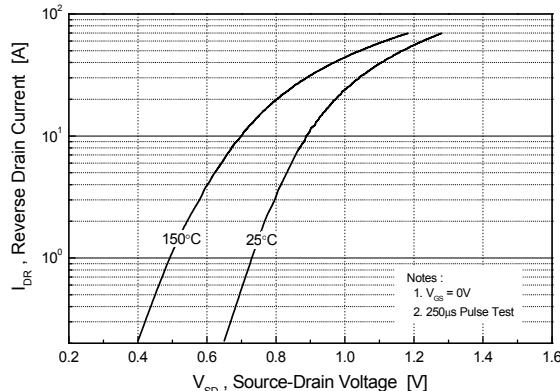


Figure 5. Capacitance Characteristics

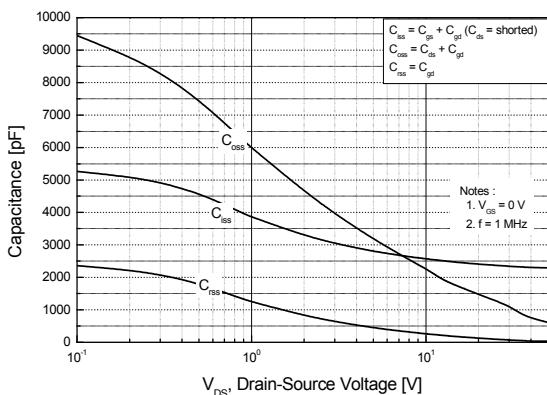
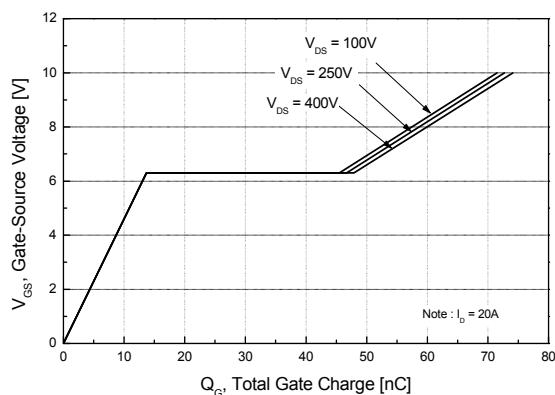


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

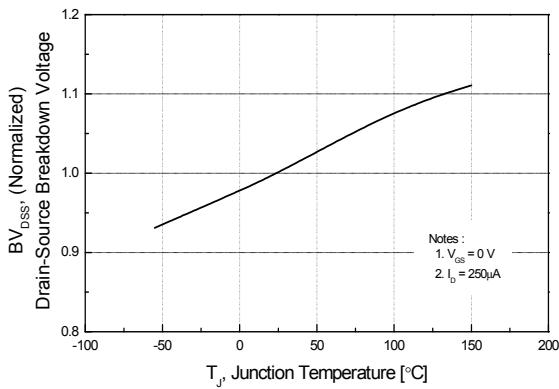


Figure 8. On-Resistance Variation vs. Temperature

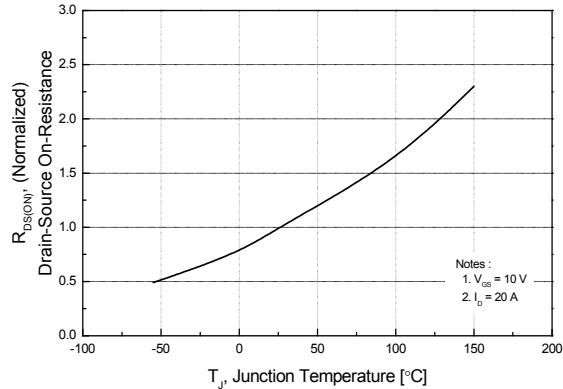


Figure 9-1. Maximum Safe Operating Area for FCP20N60

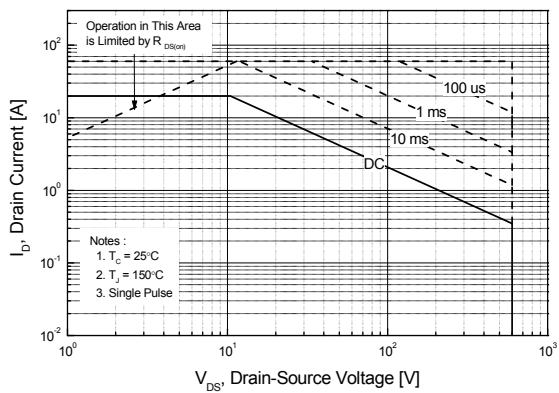


Figure 9-2. Maximum Safe Operating Area for FCPF20N60

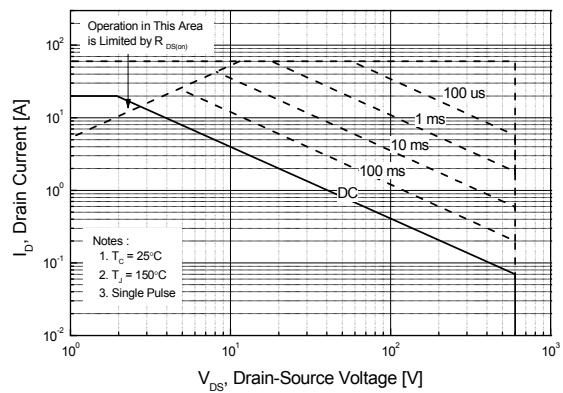
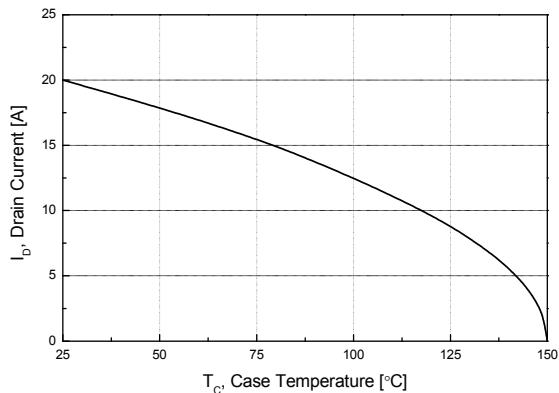


Figure 10. Maximum Drain Current vs. Case Temperature



Typical Performance Characteristics (Continued)

Figure 11-1. Transient Thermal Response Curve for FCP20N60

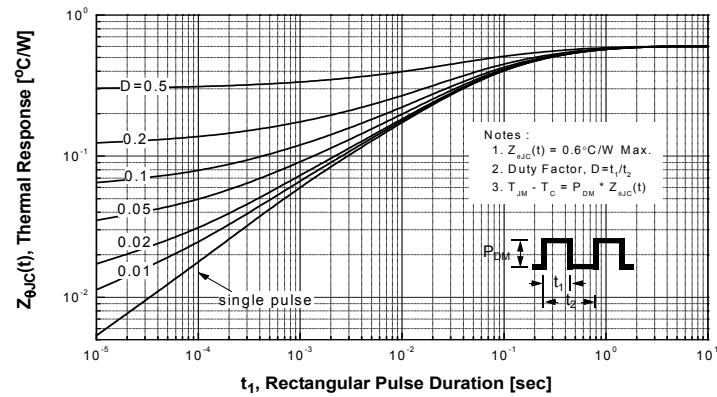
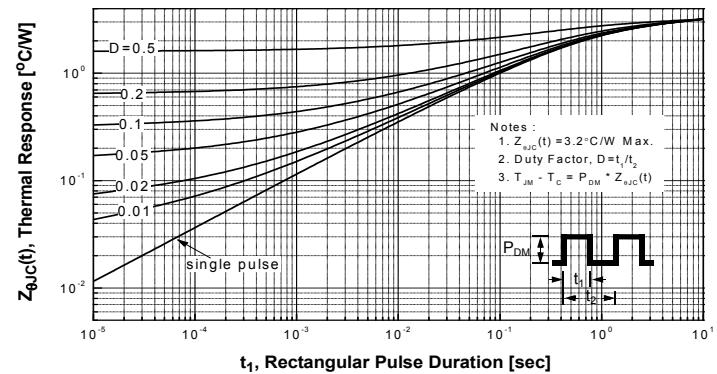


Figure 11-2. Transient Thermal Response Curve for FCPF20N60



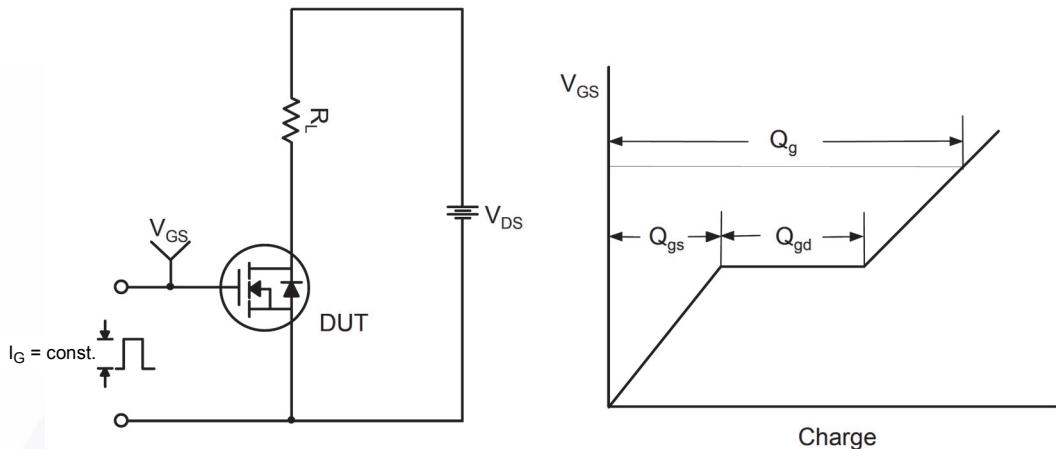


Figure 12. Gate Charge Test Circuit & Waveform

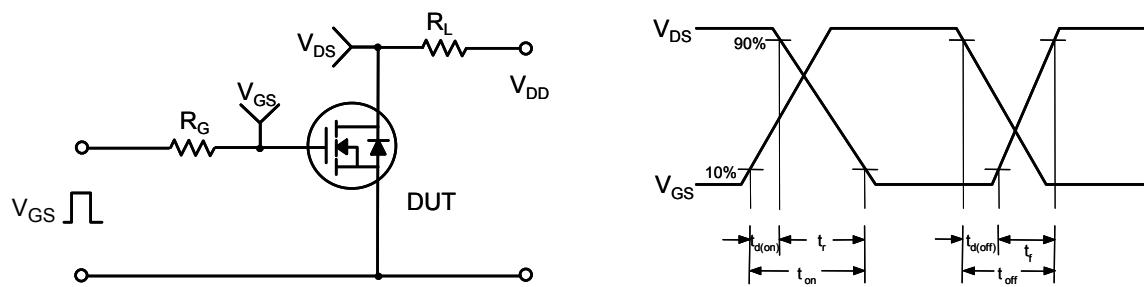


Figure 13. Resistive Switching Test Circuit & Waveforms

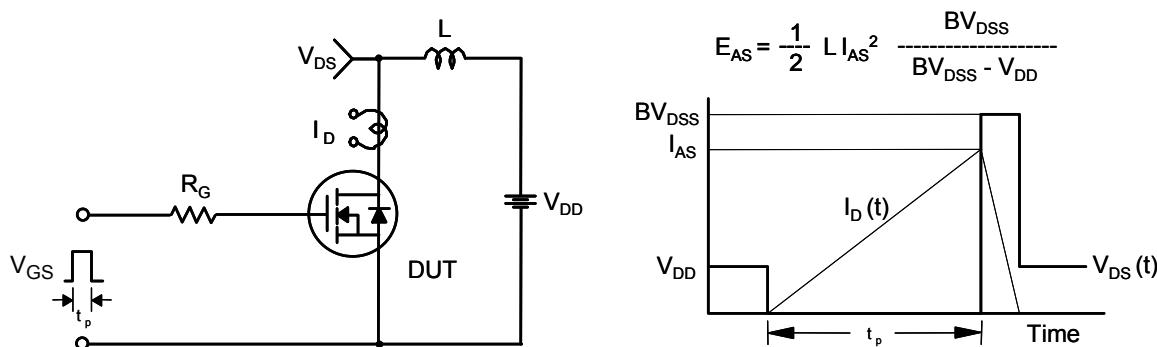


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

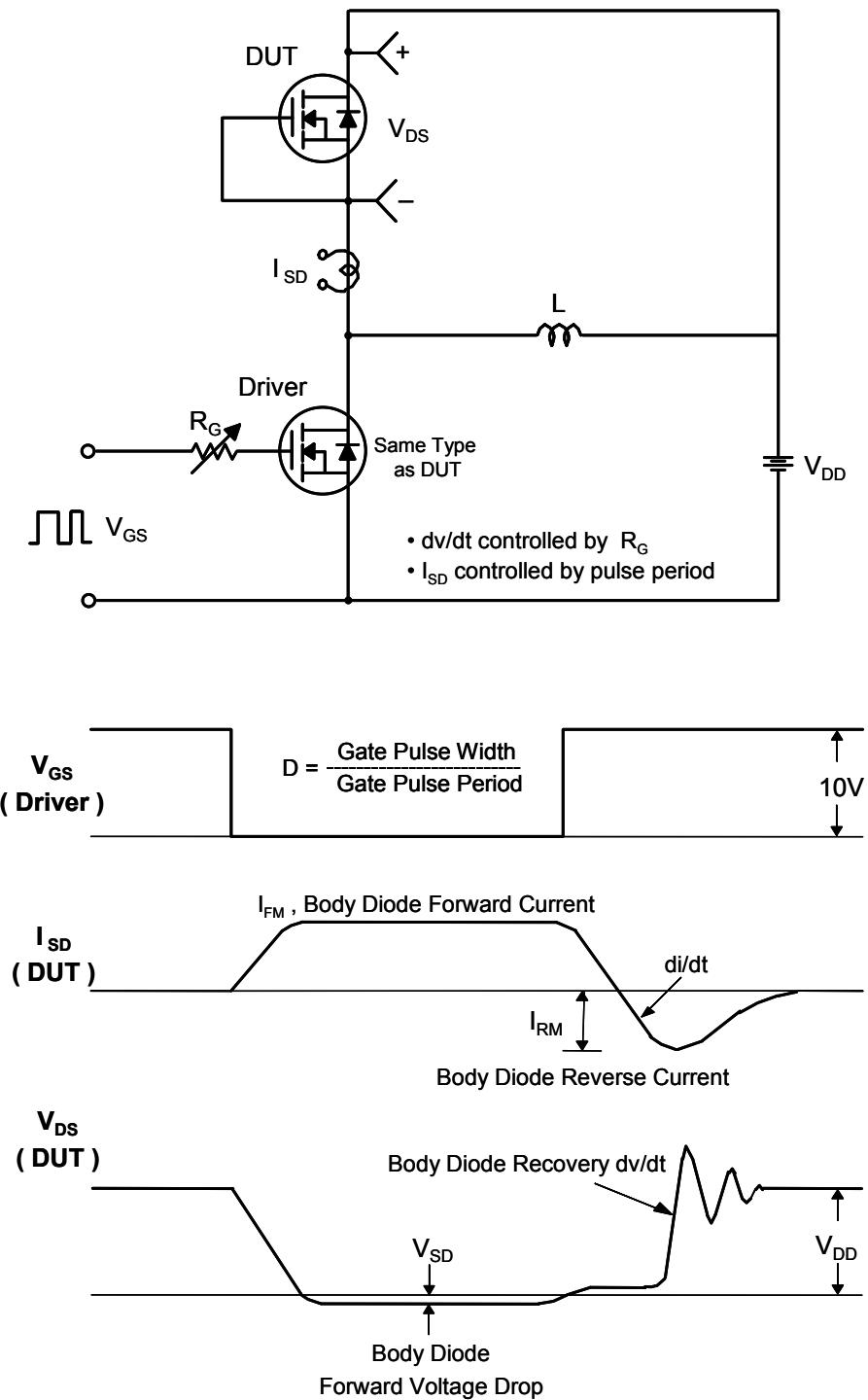
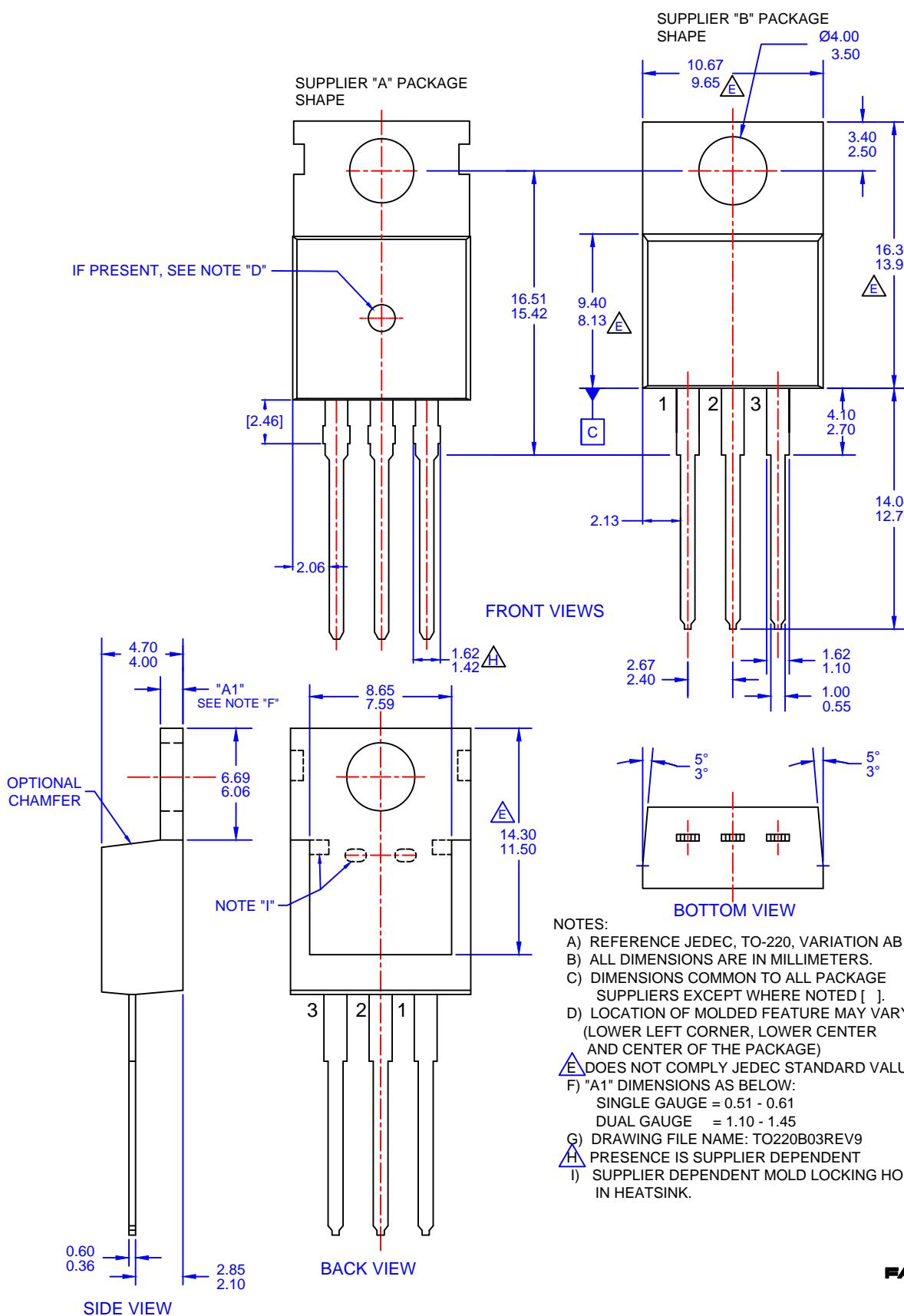
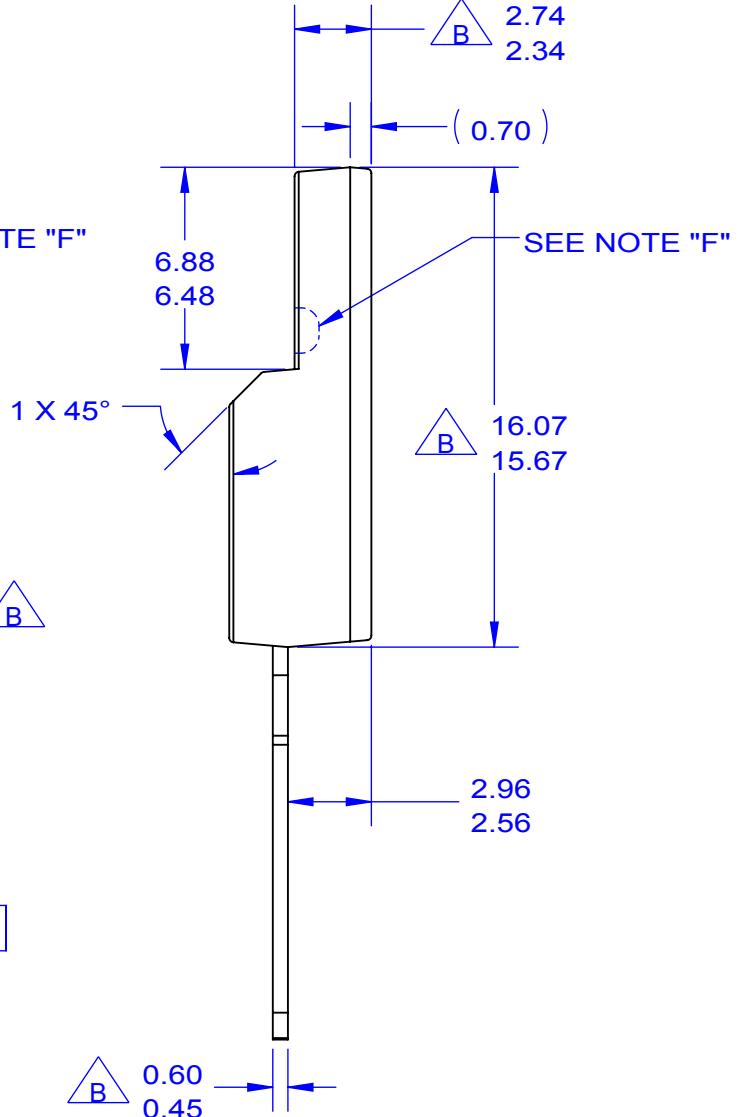
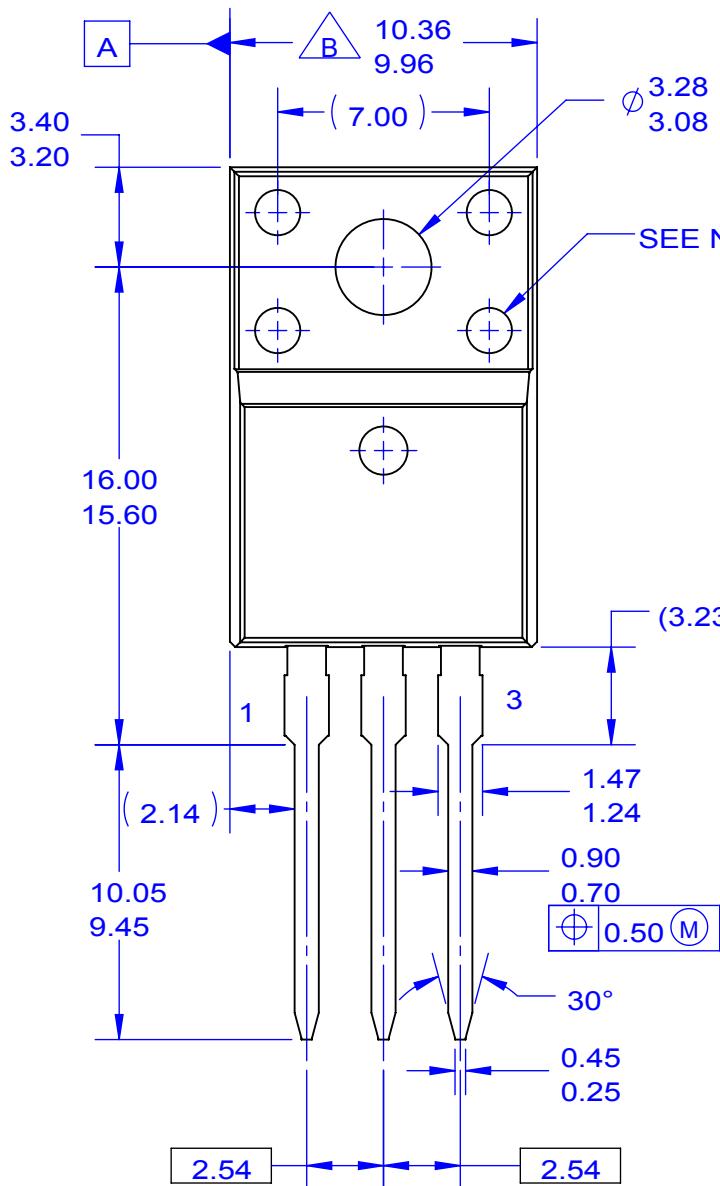


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

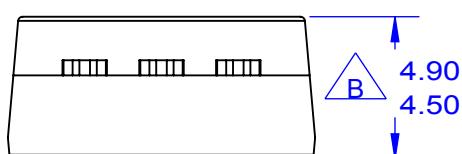


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NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. OPTION 1 - WITH SUPPORT PIN HOLE.
OPTION 2 - NO SUPPORT PIN HOLE.
- G. DRAWING FILE NAME: TO220M03REV3





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Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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